

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	4	(("6653698") or ("6352913")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/11/16 09:50
S2	0	S1 and "CMOS" and (semiconductor or wafer or substrate) and p-well and n-well and buffer and (gate near4 dielectric) and (metal or conductiv\$4) and etch\$4 and remov\$4 and anneal	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/17 10:53
S3	10	"CMOS" and (semiconductor or wafer or substrate) and p-well and n-well and buffer and (gate near4 dielectric) and (metal or conductiv\$4) and etch\$4 and remov\$4 and anneal and nitrogen and aluminum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:32
S4	1	"CMOS" and (semiconductor or wafer or substrate) and p-well and n-well and buffer and (gate near4 dielectric) and (metal or conductiv\$4) and etch\$4 and remov\$4 and anneal and nitrogen and aluminum and "sulfuric acid" and "hydrogen peroxide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 10:55
S5	1	n-mos and p-mos and (semiconductor or wafer or substrate) and p-well and n-well and buffer and (gate near4 dielectric) and (metal or conductiv\$4) and etch\$4 and remov\$4 and anneal and nitrogen and aluminum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 10:55
S6	2243	n-mos and p-mos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:33
S7	176	n-mos and p-mos and n-well and p-well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:33

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S8	6	n-mos and p-mos and n-well and p-well and ("gate dielectric" near4(semiconductor or wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:34
S9	4	n-mos and p-mos and n-well and p-well and ("gate dielectric" near4(semiconductor or wafer or substrate)) and buffer and etch and metal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:34
S10	3	n-mos and p-mos and n-well and p-well and ("gate dielectric" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:35
S11	0	n-mos and p-mos and n-well and p-well and ("gate oxide" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:35
S12	2	n-mos and p-mos and n-well and p-well and ("gate oxide" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:36
S13	156	("gate oxide" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:36
S14	29	("gate oxide" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal and p-well and n-well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:22
S15	25	"CMOS" and "aluminum nitride" and "sulfuric acid" and "hydrogen peroxide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:23

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S16	1	"CMOS" and "aluminum nitride" and "sulfuric acid" and "hydrogen peroxide" and "hydrofluoric acid" and anneal and temperature and ("PVD" or "CVD" or "ALD") and (titanium or hafnium or tantalum) and alloy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:25
S17	4	"CMOS" and "aluminum nitride" and "sulfuric acid" and "hydrogen peroxide" and "hydrofluoric acid" and anneal and temperature and ("PVD" or "CVD" or "ALD") and (titanium or hafnium or tantalum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:53
S18	1	"CMOS" and "aluminum nitride" and "sulfuric acid" and "hydrogen peroxide" and "hydrofluoric acid" and anneal and temperature and ("PVD" or "CVD" or "ALD") and (titanium or hafnium or tantalum) and electronegativ\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:25
S19	921	hafnium and tantalum and titanium and "CMOS"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:53
S20	11	hafnium and tantalum and titanium and "CMOS" and "aluminum nitride" and electronegativ\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:54
S21	1	hafnium and tantalum and titanium and "CMOS" and "aluminum nitride" and electronegativ\$4 and n-mos and p-mos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:54
S22	9	hafnium and tantalum and titanium and "CMOS" and "aluminum nitride" and electronegativ\$4 and energy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:57
S23	188	hafnium and "CMOS" and "aluminum nitride" and electronegativ\$4 and energy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:57

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S24	9	hafnium and tantalum and "CMOS" and "aluminum nitride" and electronegativ\$4 and energy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:58
S25	2180	"CMOS" and "metal gate"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:59
S26	4	"CMOS" and "metal gate" and "aluminum nitride" and electronegativity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:04
S27	234	"aluminum nitride" and electronegativity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:07
S28	2	("aluminum nitride" near4 electronegativity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:06
S29	0	("aluminum nitride" near4 electronegativity) and hafnium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:06
S30	192	"aluminum nitride" and electronegativity and hafnium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:07
S31	13	"aluminum nitride" and electronegativity and hafnium and tantalum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:11

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S32	10	"metal gate" and (dielectric or oxide) and electronegativity and hafnium and tantalum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:11
S33	2	"metal gate" and (dielectric or oxide) and electronegativity and hafnium and tantalum and "aluminum nitride"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:11
S34	40177	CMOS and ((dielectric or oxide or insulat\$4) near9 (semiconducutor or substrate or wafer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 09:52
S35	0	CMOS and ((dielectric or oxide or insulat\$4) near9 (semiconducotor or substrate or wafer)) and p-well and n-well and MOSFET and ("aluminum nitride" or "AIN") and (metal near9 "buffer layer") and (etch near9 metal) and anneal\$4 and tmeperature and (PVD or ALD or CVD)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 09:55
S36	0	CMOS and ((dielectric or oxide or insulat\$4) near9 (semiconducotor or substrate or wafer)) and p-well and n-well and MOSFET and ("aluminum nitride" or "AIN") and (metal near9 "buffer layer") and (etch near9 metal) and anneal\$4 and temperature and (PVD or ALD or CVD)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 09:56
S37	0	CMOS and ((dielectric or oxide or insulat\$4) near9 (semiconducotor or substrate or wafer)) and p-well and n-well and MOSFET and ("aluminum nitride" or "AIN") and metal and (buffer near layer) and (etch near9 metal) and anneal\$4 and temperature and (PVD or ALD or CVD)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 09:57

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S38	4	CMOS and ((dielectric or oxide or insulat\$4) near9 (semiconducutor or substrate or wafer)) and p-well and n-well and MOSFET and ("aluminum nitride" or "AIN") and metal and (buffer near layer) and etch and anneal\$4 and temperature and (PVD or ALD or CVD)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:01
S39	9	"5989550"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:01
S40	13	"5989950"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:10
S41	1696	CMOS and (nmos near region) and (pmos near region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:11
S42	506	CMOS and (nmos near region) and (pmos near region) and n-well and p-well	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:11
S43	452	CMOS and (nmos near region) and (pmos near region) and n-well and p-well and (gate near(dielectric or oxide or insulat\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:12
S44	21	CMOS and (nmos near region) and (pmos near region) and n-well and p-well and (gate near(dielectric or oxide or insulat\$4)) and (metal near alloy\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:12

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S45	20	CMOS and (nmos near region) and (pmos near region) and n-well and p-well and (gate near(dielectric or oxide or insulat\$4)) and (metal near alloy\$4) and (aluminum nitride or "AIN")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:13
S46	14	CMOS and (nmos near region) and (pmos near region) and n-well and p-well and (gate near(dielectric or oxide or insulat\$4)) and (metal near alloy\$4) and (aluminum nitride or "AIN") and (anneal\$4 or thermal or heat\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:13
S47	8	CMOS and (nmos near region) and (pmos near region) and n-well and p-well and (gate near(dielectric or oxide or insulat\$4)) and (metal near alloy\$4) and (aluminum nitride or "AIN") and (anneal\$4 or thermal or heat\$4) and hafnium and tantalum	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:14
S48	6	CMOS and (nmos near region) and (pmos near region) and n-well and p-well and (gate near(dielectric or oxide or insulat\$4)) and (metal near alloy\$4) and (aluminum nitride or "AIN") and (anneal\$4 or thermal or heat\$4) and hafnium and tantalum and (metal near gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:27
S49	46	(metal near gate) and ("aluminum nitride" or "AIN") near9 buffer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:32
S50	30	(metal near gate) and ("aluminum nitride" or "AIN") near9 buffer and (gate near(dielectric or oxide or insulat\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:32

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S51	13	(metal near gate) and (("aluminum nitride" or "AIN") near9 buffer) and (gate near(dielectric or oxide or insulat\$4)) and (metal near9 buffer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:33
S52	5	(metal near gate) and (("aluminum nitride" or "AIN") near9 buffer) and (gate near(dielectric or oxide or insulat\$4)) and (metal near9 buffer) and ((anneal or heat) near9 buffer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:34
S53	2	(metal near gate) and (("aluminum nitride" or "AIN") near9 buffer) and (gate near(dielectric or oxide or insulat\$4)) and (metal near9 buffer) and ((anneal or heat) near9 buffer) and alloy	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:33
S54	8	(metal near gate) and (("aluminum nitride" or "AIN") near9 buffer) and (gate near(dielectric or oxide or insulat\$4)) and (metal near9 buffer) and (anneal or heat)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:34
S55	20	(metal near gate) and (("aluminum nitride" or "AIN") near9 buffer) and (gate near(dielectric or oxide or insulat\$4)) and metal and (anneal or heat)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:40
S56	198	(metal near gate) and ("aluminum nitride" or "AIN") and (gate near(dielectric or oxide or insulat\$4)) and metal and (anneal or heat)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:42
S57	122	(metal near gate) and ("aluminum nitride" or "AIN") and (gate near(dielectric or oxide or insulat\$4)) and metal and (anneal or heat) and cmos	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:43

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S58	35	(metal near gate) and ("aluminum nitride" or "AlN") and (gate near(dielectric or oxide or insulator)) and metal and (anneal or heat) and cmos and nmos and pmos	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:57
S59	3357	(metal near gate) and CMOS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:13
S60	2517	(metal near gate) and CMOS and (gate near (dielectric or oxide or insulator))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:13
S61	5	(metal near gate) and CMOS and (gate near (dielectric or oxide or insulator)) and nmos and pmos and ("aluminum nitride" or "AlN") and electronegativity	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:16
S62	4	(metal near gate) and CMOS and (gate near (dielectric or oxide or insulator)) and nmos and pmos and ("aluminum nitride" or "AlN") and electronegativity and hafnium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:24
S63	9	(metal near gate) and CMOS and (gate near (dielectric or oxide or insulator)) and ("aluminum nitride" or "AlN") and electronegativity	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:37
S64	14	"6506676"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:47

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S65	5	(metal near gate) and ("aluminum nitride" or "AlN") and (gate near(dielectric or oxide or insulat\$4)) and metal and (anneal or heat) and cmos and nmos and pmos and electronegativity	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:58
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